

# NPN SILICON RF POWER TRANSISTOR

**DESCRIPTION:**

The ASI AVD075F is Designed for

**FEATURES:**

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- **Omnigold™** Metalization System

**MAXIMUM RATINGS**

<b>I<sub>C</sub></b>	6.5 A PEAK
<b>V<sub>CB</sub></b>	55 V
<b>P<sub>DISS</sub></b>	250 W PEAK
<b>T<sub>J</sub></b>	-65 °C to +200 °C
<b>T<sub>STG</sub></b>	-65 °C to +150 °C
<b>θ<sub>JC</sub></b>	0.7 °C/W

**PACKAGE STYLE .250 2L FLG (B)**

DIM	MINIMUM inches / mm	MAXIMUM inches / mm
A	.095 / 2.41	.105 / 2.67
B	1.050 / 26.67	
C	.245 / 6.22	.255 / 6.48
D	.120 / 3.05	.140 / 3.56
E	.552 / 14.02	.572 / 14.53
F	.790 / 20.07	.810 / 20.57
G		.285 / 7.24
H	.003 / 0.08	.007 / 0.18
I	.052 / 1.32	.072 / 1.83
J	.120 / 3.05	.130 / 3.30
K		.210 / 5.33

**ORDER CODE: ASI10560**

**CHARACTERISTICS**  $T_C = 25\text{ }^\circ\text{C}$ 

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
<b>BV<sub>CBO</sub></b>	I <sub>C</sub> = 10 mA	65			V
<b>BV<sub>CER</sub></b>	I <sub>C</sub> = 10 mA      R <sub>BE</sub> = 10 Ω	65			V
<b>BV<sub>EBO</sub></b>	I <sub>E</sub> = 1 mA	3.5			V
<b>I<sub>CES</sub></b>	V <sub>CE</sub> = 50 V			6.25	mA
<b>h<sub>FE</sub></b>	V <sub>CE</sub> = 5.0 V      I <sub>C</sub> = 500 mA	15		120	---
<b>P<sub>G</sub></b>	V <sub>CC</sub> = 50 V      P <sub>OUT</sub> = 75 W      f = 1025 - 1150 MHz	7.5			dB
<b>η<sub>C</sub></b>		35			%